

isc Silicon PNP Power Transistor

2SA614

DESCRIPTION

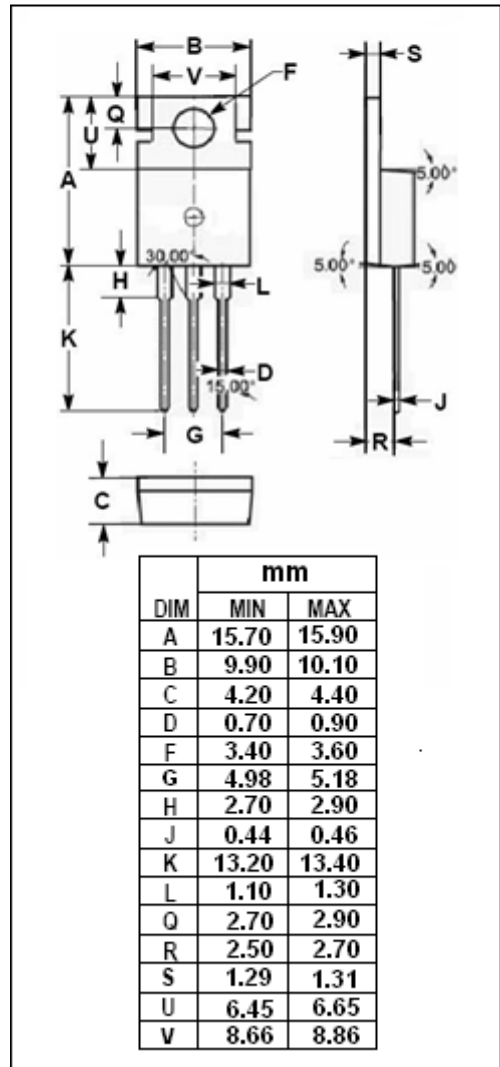
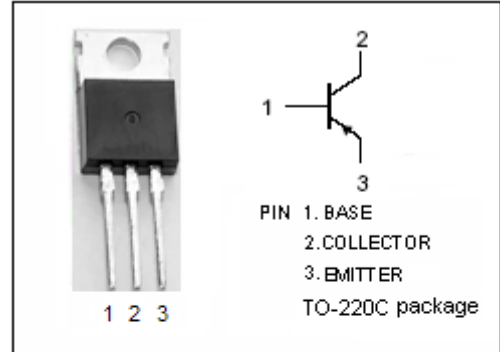
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -55V$ (Min.)
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = -0.5V$ (Max.) @ $I_C = -1A$
- Collector Power Dissipation-
: $P_C = 25W$ @ $T_C = 25^\circ C$

APPLICATIONS

- Designed for medium power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-55	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-3	A
P_C	Collector Power Dissipation	25	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



isc Silicon PNP Power Transistor**2SA614****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}; I_B = 0$	-55			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -500\ \mu\text{A}; I_E = 0$	-80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -500\ \mu\text{A}; I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -1\text{A}; I_B = -0.1\text{A}$			-0.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -80\text{V}; I_E = 0$			-50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5; I_C = 0$			-50	μA
h_{FE}	DC Current Gain	$I_C = -0.5\text{A}; V_{CE} = -5\text{V}$	40		240	

◆ **h_{FE} Classifications**

R	O	Y
40-80	70-140	120-240